

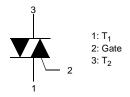
February 2008

FKN08PN60S TRIAC (Silicon Bidirectional Thyristor)

Application Explanation

- Switching mode power supply, light dimmer, electric flasher unit, hair drier
- TV sets, stereo, refrigerator, washing machine
- · Electric blanket, solenoid driver, small motor control
- Photo copier, electric tool





Absolute Maximum Ratings Ta = 25°C unless otherwise noted

Symbol	Parameter	Value		Rating	Units
V _{DRM} V _{RRM}	Peak Repetitive Off-State Voltage	Sine Wave 50 to 60Hz, Gate Open		600	V
I _{T (RMS)}	RMS On-State Current	Commercial frequency, sine full wave 360° conduction, Tc= 70 ℃		0.8	А
I _{TSM}	Surge On-State Current	Sinewave half cycle, peak value, non-repetitive	60Hz	8	А
l ² t	I ² t for Fusing	Value corresponding to halfwave, surge on-state current, tp=8.33ms		0.26	A ² s
P _{GM}	Peak Gate Power Dissipation			5	W
P _{G (AV)}	Average Gate Power Dissipation			0.1	W
V_{GM}	Peak Gate Voltage			5	V
I _{GM}	Peak Gate Current			1	А
T _J	Junction Temperature			- 40 ~ 125	°C
T _{STG}	Storage Temperature			- 40 ~ 125	°C

Thermal Characteristics

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case ^(note1)	45	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ^(note2)	160	°C/W

1

Note1: Infinite cooling condition.

Note2: JESD51-10 (Test Borad: FR4 3.0"*4.5"*0.062", Minimum land pad)

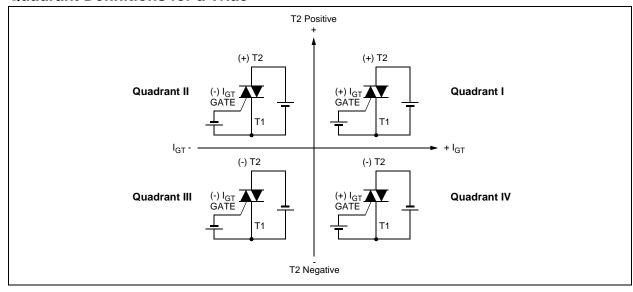
Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter		Test Condition		Min.	Тур.	Max.	Units
I _{DRM} I _{RRM}	Repetieive Peak Off-State Curre	nt	V _{DRM} /V _{RRM} applied		-	-	100	μА
V _{TM}	On-State Voltage		T _C =25°C, I _{TM} =1.12A Instantaneous measurement		-	-	1.8	V
	Gate Trigger Voltage (Note 2)	- 1		T2(+), Gate (+)	-	-	2.0	V
V_{GT}		II	$V_D=12V$, $R_L=100\Omega$	T2(+), Gate (-)	-	-	2.0	V
		III		T2(-), Gate (-)	-	-	2.0	V
	Gate Trigger Current (Note 2)	I		T2(+), Gate (+)	-	-	5	mA
I_{GT}		II	$V_D = 12V, R_L = 100\Omega$	T2(+), Gate (-)	-	-	5	mA
		III		T2(-), Gate (-)	-	-	5	mA
V_{GD}	Gate Non-Trigger Voltage		T _J =125°C, V _D =1/2V _{DRM}		0.2	-	-	V
I _H	Holding Current (I, II,III)		V _D = 12V, I _{TM} = 200mA		-	-	15	mA
IL	Latching Current	I, III	$V_D = 12V, I_G = 10mA$		-	-	15	mA
		П]		-	-	20	mA
dv/dt(s)	Critical Rate of Rise of Off-State Voltag		V_{DRM} = 63% Rated, T_j = 125°C, Exponential Rise		20	-	-	V/µs
dv/dt(c)	Critical-Rate of Rise of Off-State Commutating Voltage (di/dt=-0.7A/uS)				3.0	-	-	V/µs

Commutation dv/dt test

V _{DRM} (V)	Test Condition	Commutating voltage and current waveforms (inductive load)
FKN08PN60S	1. Junction Temperature T _J =125°C 2. Rate of decay of on-state commutating current (di/dt) _C 3. Peak off-state voltage V _D = 300V	Supply Voltage Time Main Current Main Voltage (dv/dt) _C Time V _D

Quadrant Definitions for a Triac



Package Marking and Ordering Information

Device Marking	Device	Package	Packing	Tape Width	Quantity
K08PN60S	FKN08PN60S	TO-92	BULK		

Typical Performance Characteristics

Figure 1. On-State Characteristics

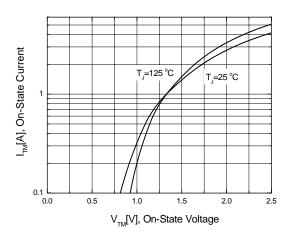


Figure 3. RMS Current Rating

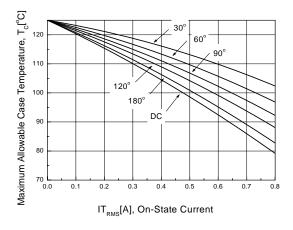


Figure 5. Typical Gate Voltage vs Junction Temperarure

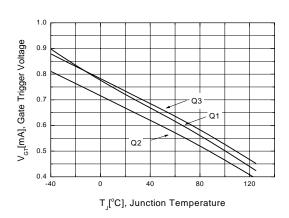


Figure 2. Power Dissipation

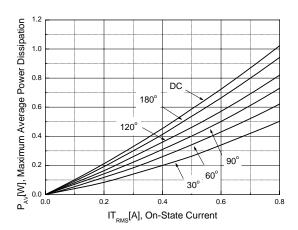


Figure 4. Typical Gate Trigger Current vs Junction Temperature

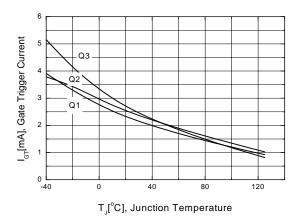
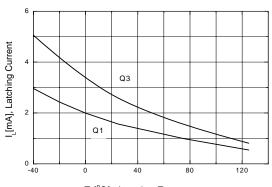


Figure 6. Typical Latching Currrent vs Junction Temperature



T_J[°C], Junction Temperature

Typical Performance Characteristics (Continued)

Figure 7. Typical Holding Current vs Junction Temperature

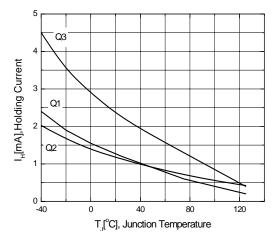
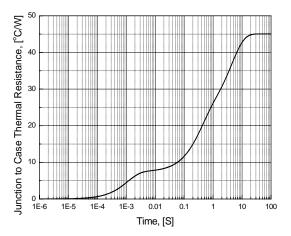
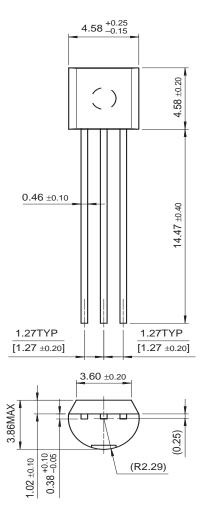


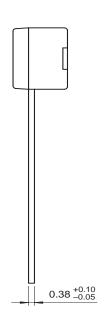
Figure8. Junction to Case Thermal Resistance



Package Dimension

TO-92









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